

Description

The 20P03-HXY uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a

Battery protection or in other Switching application.



TO252-2L

General Features

 $V_{DS} = -30V I_{D} = -20A$

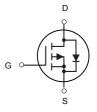
 $R_{DS(ON)}$ < 42 m Ω @ V_{GS} =10V

Application

Battery protection

Load switch

Uninterruptible power supply



P-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
20P03-HXY	TO252-2L	20P03 XXX YYYY	2500

Absolute Maximum Ratings (T_c=25°C unless otherwise noted)

Symbol	Parameter Rating		Units	
VDS	Drain-Source Voltage	-30	V	
VGS	Gate-Source Voltage	±25	V	
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ 10V ¹	Drain Current, V _{GS} @ 10V ¹ -20		
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ 10V ¹	-15	А	
IDM	Pulsed Drain Current ²	-50	А	
P _D @T _C =25°C	Total Power Dissipation⁴	29	W	
TSTG	Storage Temperature Range	-55 to 150	°C	
TJ	Operating Junction Temperature Range	-55 to 150	°C	
R⊕JA	Thermal Resistance Junction-ambient ¹	75	°C/W	
R₀JC	Thermal Resistance Junction-Case ¹	4.32 °C/W		



Electrical Characteristics (T_A=25 ℃ unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тр	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	VGS=0V , ID=-250uA	-30			V
∆BVDSS/∆TJ	BVDSS Temperature Coefficient	Reference to 25°C , ID=-1mA		22		V/°C
RDS(ON)	Static Drain-Source On-Resistance2	VGS=-10V , ID=-15A	32	38	42	mΩ
		VGS=-4.5V , ID=-10A	48	60	70	
VGS(th)	Gate Threshold Voltage	VGS=VDS , ID =-250uA			-2.5	V
△VGS(th)	VGS(th) Temperature Coefficient			4.6		mV/°C
		VDS=-24V , VGS=0V ,			-1	
IDSS		TJ=25℃				١.
	-Drain-Source Leakage Current	VDS=-24V , VGS=0V ,			-5	uA
		TJ=55℃				
IGSS	Gate-Source	VGS=±25V , VDS=0V			±100	nA
	LeakageCurrent					
gfs	Forward	VDS=-5V , ID=-15A		19		S
Rg	Transconductance Gate Resistance	VDS=0V , VGS=0V , f=1MHz		13		
Qg	Total Gate Charge (-4.5V)			12.5		
Qgs	Gate-Source Charge	 VDS=-15V , VGS=-4.5V , ID=-15A		5.4		nC
Qgd	Gate-Drain Charge	1		5		
Td(on)	Turn-On Delay Time			4.4		
Tr	Rise Time	VDD=-15V , VGS=-10V , RG=3.3 , ID=-15A		11.2		ns
Td(off)	Turn-Off Delay Time			34		
Tf	Fall Time			18		
Ciss	Input Capacitance	VDS=-15V , VGS=0V , f=1MHz		1345		pF
Coss	Output Capacitance			194		
Crss	Reverse Transfer Capacitance			158		

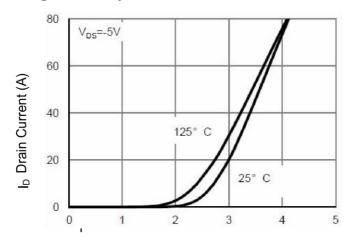
Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- **3.** Pulse Test: Pulse Width ≤ 300μ s, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production

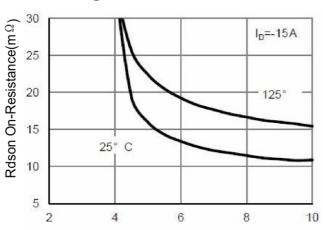


Typical Electrical and Thermal Characteristics

Figure 5 Output Characteristics



Vgs Gate-Source Voltage (V)
Figure 7 Transfer Characteristics



Vgs Gate-Source Voltage (V)
Figure 9 Rdson vs Vgs

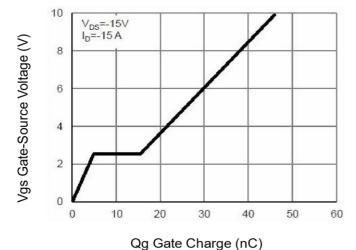
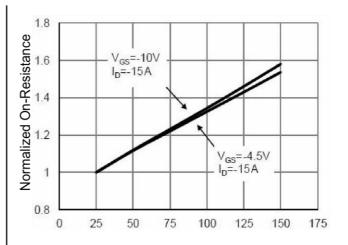
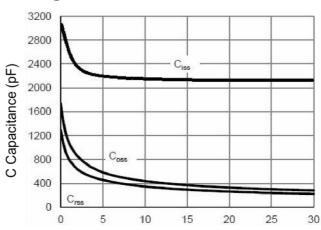


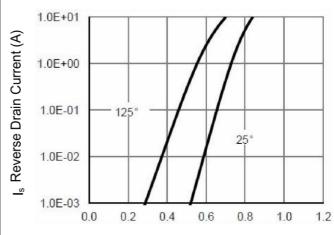
Figure 11 Gate Charge



 T_J -Junction Temperature(${}^{\circ}$ C) Figure 8 Drain-Source On-Resistance



Vds Drain-Source Voltage (V)
Figure 10 Capacitance vs Vds



Vsd Source-Drain Voltage (V)
Figure 12 Source- Drain Diode Forward



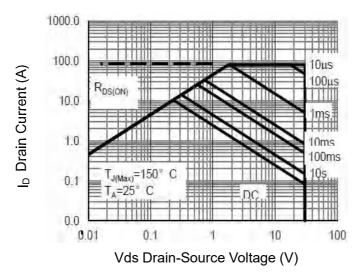


Figure 13 Safe Operation Area

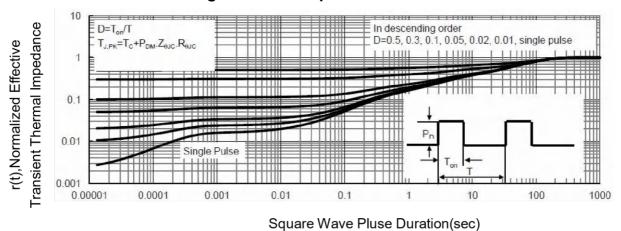
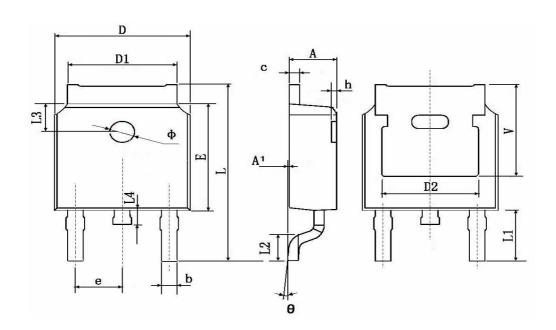


Figure 14 Normalized Maximum Transient Thermal Impedance



TO252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches			
	Min.	Max.	Min.	Max.		
A	2.200	2.400	0.087	0.094		
A1	0.000	0.127	0.000	0.005		
b	0.660	0.860	0.026	0.034		
С	0.460	0.580	0.018	0.023		
D	6.500	6.700	0.256	0.264		
D1	5.100	5.460	0.201	0.215		
D2	4.83	4.830 TYP.		0.190 TYP.		
E	6.000	6.200	0.236	0.244		
е	2.186	2.386	0.086	0.094		
L	9.800	10.400	0.386	0.409		
L1	2.90	2.900 TYP.		0.114 TYP.		
L2	1.400	1.700	0.055	0.067		
L3	1.600 TYP.		0.063 TYP.			
L4	0.600	1.000	0.024	0.039		
Ф	1.100	1.300	0.043	0.051		
θ	0°	8°	0°	8°		
h	0.000	0.300	0.000	0.012		
V	5.35	0 TYP.	YP. 0.211 TYP.			

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